

# RSC Advances



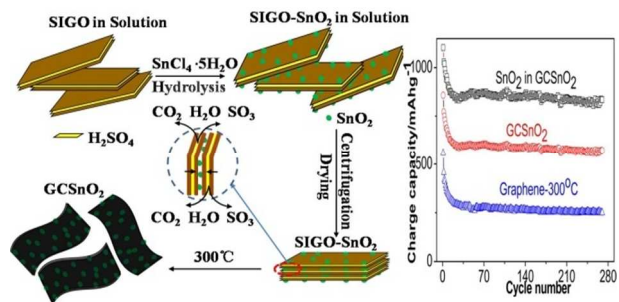
This is an *Accepted Manuscript*, which has been through the Royal Society of Chemistry peer review process and has been accepted for publication.

*Accepted Manuscripts* are published online shortly after acceptance, before technical editing, formatting and proof reading. Using this free service, authors can make their results available to the community, in citable form, before we publish the edited article. This *Accepted Manuscript* will be replaced by the edited, formatted and paginated article as soon as this is available.

You can find more information about *Accepted Manuscripts* in the [Information for Authors](#).

Please note that technical editing may introduce minor changes to the text and/or graphics, which may alter content. The journal's standard [Terms & Conditions](#) and the [Ethical guidelines](#) still apply. In no event shall the Royal Society of Chemistry be held responsible for any errors or omissions in this *Accepted Manuscript* or any consequences arising from the use of any information it contains.

## Table of contents



Facile preparation of high-performance graphene/SnO<sub>2</sub> nano-composites for Li-ion batteries based on expansion and exfoliation of SIGO is demonstrated.

## ARTICLE

## Facile Synthesis of Graphene Clamped SnO<sub>2</sub> Nanostructured Materials for Lithium-Ion Batteries

Cite this: DOI: 10.1039/x0xx00000x

Yanzhong Hong,<sup>1</sup> Jianyin Zhang,<sup>1</sup> Zhiyong Wang,<sup>1\*</sup> Joseph J. Stankovich,<sup>2</sup> and Xianbo Jin<sup>1,2\*</sup>

Received 00th January 2012,  
Accepted 00th January 2012

DOI: 10.1039/x0xx00000x

www.rsc.org/

Graphene-based composite materials have attracted considerable interest due to their dramatic performance in various applications. However, the present synthesis processes, usually via graphene oxide (GO), are still very expensive. Here we propose an easy and affordable strategy based on sulfuric acid intercalated GO (SIGO) for the preparation of graphene clamped nano-SnO<sub>2</sub> (GCSnO<sub>2</sub>) with high performance for lithium-ion batteries. SIGO is the direct and readily available intermediate product during the oxidation of graphite in sulfuric acid, but has been overlooked for nearly a century. In the past, SIGO was washed to clean GO with great difficulties. An interesting characteristic of SIGO that we have found is its easy expansion and exfoliation to high quality graphene at very low temperatures (just above 100 °C). In this work, GCSnO<sub>2</sub> containing 55 wt % SnO<sub>2</sub> nanoparticles (5–10 nm in diameters) has been prepared by expansion and exfoliation of nano-SnO<sub>2</sub> coated SIGO at 300 °C in air. The samples have been characterized by X-ray diffraction (XRD), scanning electron microscopy (SEM), transmission electron microscopy (TEM) and thermogravimetric analysis (TGA). The initial reversible charge/discharge capacity of GCSnO<sub>2</sub> was 858 mAh/g at a current density of 200 mAh/g in the potential range between 0.02 and 2.00 V. The capacity decayed to about 600 mAh/g after 10 cycles and then kept almost unchanged and 572 mAh/g remained after the studied 270 cycles. The contribution of SnO<sub>2</sub> was estimated to be about 800 mAh/g during cycling, corresponding to the full and stable utilization of the theoretical capacity of SnO<sub>2</sub>.

Keywords: SnO<sub>2</sub>, graphene, SIGO, anode materials, lithium-ion batteries.

### Introduction

SnO<sub>2</sub>, an n-type semiconductor, is one of the most intensively investigated materials due to its wide applications in such as gas sensors, transistors, batteries and electron emitters.<sup>1–4</sup> SnO<sub>2</sub> is also a promising alternative anode material for lithium-ion batteries because it is safe and can store large amounts with high of energy. Lithium-ion batteries are widely used as mobile power sources for everyday portable electric devices such as phones, laptops, and ipods. They also have potential uses for clean electrical/hybrid vehicles.<sup>5,6</sup> The graphite anode, used in current lithium-ion batteries, suffers from relatively low theoretical gravimetric capacity (372 mAh/g), which cannot meet the demand for high specific capacity applications, particularly in hybrid vehicles. SnO<sub>2</sub> shows a two-step reaction mechanism: (1) SnO<sub>2</sub> + 4 Li → 2Li<sub>2</sub>O + Sn and (2) Sn + 4.4Li ↔ Li<sub>4.4</sub>Sn, and the second step gives SnO<sub>2</sub> a theoretical reversible capacity of as high as 782 mAh/g, which is more than twice of graphite. Other advantages of SnO<sub>2</sub> include low discharge potential (<1.5 V), low cost, and the high abundance of natural resources.<sup>7,8</sup>

Nevertheless, bulky SnO<sub>2</sub> is unsuitable for electrode application due to its enormous volume expansion (>300%) during the Sn-Li alloy process. This expansion may cause the pulverization of

the active materials, leading to loss of electrical contact in the electrode, consequently poor cyclic stability.<sup>9,10</sup> Using nanostructured porous SnO<sub>2</sub> as the active material or constructing a porous electrode with in-situ pores around the Sn nano-particles may improve the cycling performance.<sup>11,12</sup> Another approach is to mix nano-SnO<sub>2</sub> with some buffer materials.<sup>13,14</sup> Graphene, a new two-dimensional carbon material with high conductivity, has attracted considerable interest in recent years.<sup>15</sup> Graphene has a theoretical specific surface area of over 2600 m<sup>2</sup>/g, thus it could be a ideal matrix to disperse and anchor metal-oxide nanoparticles.<sup>16</sup> It has been demonstrated that SnO<sub>2</sub>/graphene nanostructures can provide an effective volume buffer and prevent the Sn nanoparticle from aggregation, consequently showing high cycling stability as reported recently.<sup>17–19</sup> Some further structural designs, for example coating the SnO<sub>2</sub> nanoparticles in SnO<sub>2</sub>/graphene composites with S or C, have also been reported for improved electrochemical performance.<sup>20–21</sup>

However, the preparation of nano-SnO<sub>2</sub>/graphene materials remains challenging. The common synthesis route includes chemical reduction or hydrothermal reduction of nano-SnO<sub>2</sub>/GO composites in solution.<sup>22–26</sup> There are several disadvantages for these routes. GO is usually prepared by the

reaction between graphite and strong oxidants in concentrated sulfuric acid. The separation of GO from the acid system was usually conducted by tedious rinsing with water and hydrochloric acid, thus increasing the workload and the amount of waste acid.<sup>27-29</sup> In chemical reduction processes, expensive and hazardous reductants (such as hydrazine) have been used to reduce the GO, further increasing the expense and making the process less environmentally friendly.<sup>29-31</sup> Lastly, the separation of SnO<sub>2</sub>/GO or SnO<sub>2</sub>/graphene from the solution is also difficult. A direct drying often leads to hard lumps of SnO<sub>2</sub>/graphene due to the inevitable aggregation and, subsequently poor electroactivity. However, vacuum freeze drying or vacuum assistant thermal treatment can produce powders of nano-SnO<sub>2</sub>/graphene which are favorable in electrode applications, these processes are energy intensive.<sup>32,33</sup> The nano-SnO<sub>2</sub>/graphene may also be prepared by coating nano-SnO<sub>2</sub> on graphene sheets. Despite difficulties listed above, great efforts should be made to disperse the graphene into a solvent.<sup>34-38</sup>

To address these problems, we propose an effective strategy for the preparation of graphene clamped nano-SnO<sub>2</sub> (GCSnO<sub>2</sub>) by taking advantage of low temperature expansion and exfoliation of the sulfuric acid intercalated graphite oxide (SIGO).<sup>39</sup> SIGO is the most direct and readily available oxidation product of graphite in sulfuric acid. Although SIGO is a long-existing species in the GO chemistry, its application for graphene or graphene based materials has not been considered. We found SIGO with a sulfuric acid content of about 15 wt.% can undergo rapid expansion and exfoliation to high quality graphene at very low temperatures (just above 100 °C).<sup>39</sup> In this work, high-performance GCSnO<sub>2</sub> anode materials were prepared by low temperature expansion of nano-SnO<sub>2</sub> coated SIGO. The nano-SnO<sub>2</sub> can deliver a reversible capacity as high as 800 mAh/g during the examined 270 cycles at a current density of 200 mA/g. This result corresponds to the stable and nearly full utilization of the theoretical reversible capacity of SnO<sub>2</sub> for the lithium-ion batteries.

## Experimental

### Materials:

Natural graphite flakes with a mean size of 30 μm were supplied by Shanghai Colloid Chemical Factory (China). Potassium permanganate (KMnO<sub>4</sub>, 99.5%), sulfuric acid (H<sub>2</sub>SO<sub>4</sub>, 98%), sodium nitrate (NaNO<sub>3</sub>, 99.0%), SnCl<sub>4</sub>·5H<sub>2</sub>O (AR), hydrogen peroxide (H<sub>2</sub>O<sub>2</sub>, 30%), and hydrochloric acid (HCl, 37%), were purchased from Sinopharm Chemical Reagent Co., Ltd. (China). High-purity deionized water (18.5 MΩ cm) was prepared by water purifier (Chengdu Pincheng Technology Co., Ltd.).

### Preparation of SIGO:

SIGO was synthesized according to our previous report.<sup>39</sup> Graphite was oxidized in concentrated sulfuric acid containing KMnO<sub>4</sub> and NaNO<sub>3</sub>,<sup>40</sup> then the slurry sediment that consisted of residual H<sub>2</sub>SO<sub>4</sub> solution and SIGO was collected. Unlike in a traditional process for pure GO, where the sediment is washed by repeatedly rinsing with water and hydrochloric acid; here only slightly washing (~4 times) with a small amount of 2 wt. % hydrochloric acid solution was carried out to remove the

free H<sub>2</sub>SO<sub>4</sub>, and the resultant SIGO contained about 15 wt. % H<sub>2</sub>SO<sub>4</sub>.

### Preparation of Graphene Clamped Nano-SnO<sub>2</sub> (GCSnO<sub>2</sub>):

Approximately 0.5 g SIGO was dispersed in 80 ml H<sub>2</sub>O, then 400 mg SnCl<sub>4</sub>·5H<sub>2</sub>O was added under continuous agitation. The hydrolyzation of SnCl<sub>4</sub> lasted 12 h at room temperature. After drying in air at 50 °C, the synthesized SnO<sub>2</sub>/SIGO composite was loaded into the bottom of a quartz tube that has a side pipe for gas emission. The tube bottom was then heated at 300 °C and a sudden expansion of the SnO<sub>2</sub>/SIGO occurred within 1 min. The temperature was maintained for 30 min before GCSnO<sub>2</sub> was collected. For comparison, pure graphene was prepared similarly from SIGO. Ordinary SnO<sub>2</sub>/graphene composite (O-G/SnO<sub>2</sub>) was prepared by hydrolyzation of SnCl<sub>4</sub> in the presence of the dispersed graphene in aqueous solution, and pure Nano-SnO<sub>2</sub> was prepared by hydrolyzation of SnCl<sub>4</sub>.

### Sample Characterization:

The structure and morphology of the as synthesized composites were characterized by X-ray diffraction (XRD, Shimadzu XRD-6000) using Cu K<sub>a</sub> radiation, scanning electron microscopy (SEM, FEI Quanta 200), and high-resolution transmission electron microscopy (HRTEM, JEOL-2100). Thermogravimetric analysis (TGA, TA-Q500) was performed from 30 to 800 °C at an elevated rate of 10 °C/min in air. X-ray photoelectron spectroscopy (XPS) analysis was carried out with a Kratos XSAM800 Ultra spectrometer. Raman analysis was performed with a Jobin Yvon HR800 Raman spectrometer. X-ray photoelectron spectra (XPS) was recorded on a Kratos XSAM800 Ultra spectrometer with an Mg K=1253.6 eV excitation source; the binding energies were calibrated by referencing the C1s peak to reduce the sample charge effect. Specific surface area analysis was conducted with a Micromeritics ASAP 2020 Analyzer (Norcross, GA) using the terms of the Brunauer, Emmett and Teller (BET) method with nitrogen adsorption. The Canon PC 1192 was used to take the photographs.

### Battery Assembling:

The electrochemical properties of the GCSnO<sub>2</sub> and the reference materials were studied in 2016-type coin cells with lithium metal foil as a counter electrode. The electrolyte is 1M LiPF<sub>6</sub>/EC+DMC+DEC (v/v/v, 1:1:1). The separator of cell was Celguard 2400. The test electrodes were the nickel foam supported rolled membranes (0.1 mm thick and ca. 3 mg/cm<sup>2</sup>) comprising 70 wt. % active material and 15 wt. % acetylene black plus 15wt. % polytetrafluoroethylene (PTFE), which have a diameter of 10 mm. The cells were assembled in a glove box filled with argon gas (VAC OMNI-lab). Charge–discharge cycling of the coin cell was galvanostatically performed at room temperature with cut-off voltages of 0.02 V and 2.00 V, which was controlled by the BTS-55 Neware Battery Testing System (Shenzhen, China). In this study, the charging and discharging processes represent Li-de-alloying and Li-alloying processes, respectively. The cyclic voltammograms (CVs) were carried out using an Autolab electrochemical station. The electrochemical impedance spectra was recorded at 2.0 V by

applying an AC signal of 10 mV in the frequency range from 100 kHz to 0.01 Hz.

## Results and discussion

The SIGO process is illustrated in Fig. 1. After the oxidation of graphite in sulfuric acid, the resulting GO has layered structure with many oxygenic and hydroxyl groups bonding to the graphene oxide sheets. These sheets interact strongly with the intercalated sulfuric acid (ISA), forming the SIGO. While removal of ISA from SIGO in a traditional GO process is quite difficult (Centrifugal washing more than ten times),<sup>26</sup> this process only requires ~4 rinses with water to remove the dissociative sulfuric acid and other impurities such as Mn species. The obtained SIGO has a sulfuric acid content of about 15 wt. %. More than 70% of the waste acid discharge during washing can be reduced.<sup>39</sup> SIGO was then dispersed in solution to allow the coating of hydrated nano-SnO<sub>2</sub> through in-situ hydrolysis of SnCl<sub>4</sub>. After drying, the nano-SnO<sub>2</sub> coated SIGO (denoting as SnO<sub>2</sub>/SIGO hereafter) was a dense lump as shown in Fig. 2a. The SnO<sub>2</sub>/SIGO can undergo quick expansion at temperatures above 200 °C, leading to form GCSnO<sub>2</sub> powders. It was determined previously that the reduction of SIGO at temperatures above 100 °C is catalyzed by ISA due to dehydration. The violent vapor generated simultaneously accounts for the expansion and exfoliation of SIGO. Meanwhile, the dehydration enthalpy decomposes the carboxyls to CO<sub>2</sub>.<sup>39</sup> In this work, it is demonstrated that sulfuric acid can decompose to gas as well at 300 °C. Since SnO<sub>2</sub> in the SnO<sub>2</sub>/SIGO composite may mainly reside between SIGO nanoparticle, it can be expected that the gas pressure in a SIGO nanoparticle would be much greater than that between two particles. The large pressure difference may lead to recombinational particles with the nano-SnO<sub>2</sub> tightly clamped by two graphene sheets (Fig. 1).

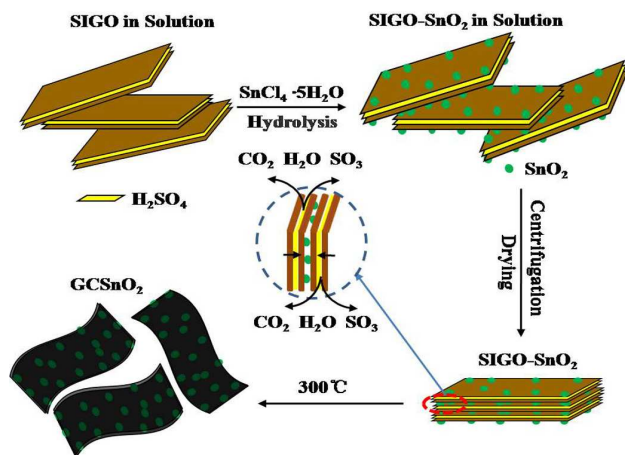


Fig. 1. a. The schematic of the SIGO process for the preparation of GCSnO<sub>2</sub>;

Single SIGO can expand in about 2 min when heated at 120 °C (Figure S1a-d), leading to a volume expansion of about 550 times. The surface area of resulting graphene was about 590 m<sup>2</sup> g<sup>-1</sup>.<sup>39</sup> The SIGO expanded more quickly at 300 °C, generating graphene with similar surface area. The expansion of SnO<sub>2</sub>/SIGO took place within 1 min at 300 °C (Figure S1e-h). As shown in Fig. 2a, the volumes of 0.5 g SnO<sub>2</sub>/SIGO and the

resultant GCSnO<sub>2</sub> are ~0.25 cm<sup>3</sup> and ~14 cm<sup>3</sup> respectively, suggesting a volume expansion of about 60 times. As shown in Fig. 2c, the GCSnO<sub>2</sub> has a specific surface area of about 237.5 m<sup>2</sup> g<sup>-1</sup>. Additionally, there are large quantities of micro-pores and meso-pores (3–50 nm) in this material (Fig. 2d), which should be favorable for the electrode applications by providing both ion passages and volume buffer. However, the SnO<sub>2</sub>/SIGO precursor only has a specific surface area of about 8.6 m<sup>2</sup> g<sup>-1</sup>, in line with its hard-lump appearance shown in Fig. 2a.

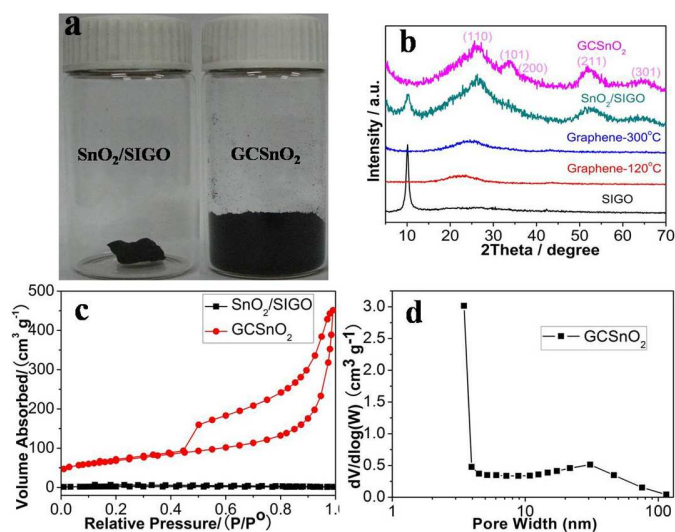


Fig. 2a. The photos of the condensed SnO<sub>2</sub>/SIGO before and after expanded to form GCSnO<sub>2</sub>. b. XRD patterns of SIGO, SnO<sub>2</sub>/SIGO, GCSnO<sub>2</sub> and graphene derived from SIGO at different temperature. c. Nitrogen adsorption–desorption isotherms for SnO<sub>2</sub>/SIGO and GCSnO<sub>2</sub>. d. pore size distribution of GCSnO<sub>2</sub>.

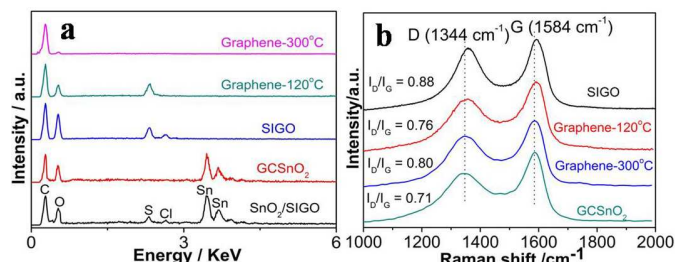


Fig. 3. a. EDX analyses of SIGO, SnO<sub>2</sub>/SIGO, GCSnO<sub>2</sub> and graphene derived from SIGO at different temperatures. b. the Raman spectra of the SIGO, graphene and GCSnO<sub>2</sub> in (a).

The XRD patterns of SIGO, SnO<sub>2</sub>/SIGO, graphene and GCSnO<sub>2</sub> are shown in Fig. 2b. The diffraction peak of SIGO at 10.6° indicates an interlayer spacing of approximately 0.83 nm, which is strong evidence of intercalation of the sulfuric acid molecules, considering that the spacing of normal GO is about 0.75 nm.<sup>25,39</sup> The 10.6° peak of the SnO<sub>2</sub>/SIGO is weaker than SIGO but still distinct. This peak disappeared in both graphene and the GCSnO<sub>2</sub>, suggesting the complete reduction and exfoliation of the SIGO and SnO<sub>2</sub>/SIGO samples after the 300 °C treatment. The broad peak at around 24.6° corresponds to the amorphous characterization of graphene. Other diffraction peaks of the prepared GCSnO<sub>2</sub> correspond to the tetragonal SnO<sub>2</sub> phase (JCPDS card no.41-1445), which are broad and weak, indicating a small particle

size of the SnO<sub>2</sub>. The particle size of SnO<sub>2</sub> was calculated from XRD according to Scherrer formula and was found to be ~8 nm. Thermal expansion of SIGO was also carried out at 120 °C for comparison and the expansion temperature showed little effect on the XRD pattern of the generated graphene.

Energy dispersive spectra analysis (EDX) was carried out to understand the SIGO process. It can be estimated from Fig. 3a that the S contents in the SIGO and SnO<sub>2</sub>/SIGO are about 5.0 wt. % and 2.6 wt. %, corresponding to H<sub>2</sub>SO<sub>4</sub> contents of about 15wt. % and 7.8 wt. %, respectively. The graphene produced at 120 °C shows a significantly lowered oxygen content with all the H<sub>2</sub>SO<sub>4</sub> remaining; suggesting the catalytic role of the ISA.<sup>37</sup> However, both the graphene and GCSnO<sub>2</sub> prepared by the thermal expansion at 300 °C are free from H<sub>2</sub>SO<sub>4</sub> due to the decomposition of H<sub>2</sub>SO<sub>4</sub>. This has been confirmed by the EDX analysis. Thus, no further washing was needed and these products were directly used for the latter anode tests. The decisive role of the intercalated sulfuric acid to the SIGO process has been confirmed. When the S content in the SIGO was lower than ~1 wt. %, neither SIGO nor SnO<sub>2</sub>/SIGO can expand at the studied temperatures (300 °C).<sup>39</sup> It was reported that traditional GO can also undergo thermal expansion but only at very high temperatures such as 900 °C.<sup>41,42</sup> This high temperature process is obviously not suitable for the preparation of SnO<sub>2</sub>/graphene due to the inevitable carbothermic reduction of SnO<sub>2</sub> to liquid Sn.

The Raman spectra of SIGO, graphene and GCSnO<sub>2</sub> exhibit two distinct peaks at around 1344 and 1584 cm<sup>-1</sup> in relation to carbon atoms (Fig. 3b). The peak at about 1584cm<sup>-1</sup>(G band) corresponds to the vibration of sp<sup>2</sup>-C=C bonds in a two-dimensional hexagonal lattice, which can be used to evaluate the degree of graphitization. The 1344cm<sup>-1</sup> peak (D band) is related to the structural defects and partially disordered structures in the hexagonal graphitic layers.<sup>43,44</sup> The intensity ratio of the D to G band, I<sub>D</sub>/I<sub>G</sub>, of SIGO was calculated as 0.88. For graphene generated at 120 °C and 300 °C, the I<sub>D</sub>/I<sub>G</sub> ratios are 0.76 and 0.80 respectively. The decreased I<sub>D</sub>/I<sub>G</sub> ratio from SIGO to graphene indicates the restoration of the sp<sup>2</sup>-bonded graphitic sheet after the thermal treatment. The possible reason for the higher I<sub>D</sub>/I<sub>G</sub> ratio of the graphene generated at 300 °C is that more oxygen-containing groups decomposed to CO<sub>2</sub> at higher temperatures, leaving more defects in the graphene.<sup>39,41</sup> The GCSnO<sub>2</sub> exhibits the lowest I<sub>D</sub>/I<sub>G</sub> ratio (0.71), suggesting the best restoration of the graphitic sheet at presence of SnO<sub>2</sub>.

As presented in Fig. 4a, the wide XPS survey spectrum of SnO<sub>2</sub>/SIGO includes signals of elements C, S, Sn, Cl, and O. The S 1s peak at about 170eV manifests the existence of sulfuric acid. After the thermal treatment at 300 °C, the S 1s peak disappeared (Fig. 4b), demonstrating the removal of sulfuric acid by decomposition. The two strong peaks located at 486.9 and 495.4 eV(also see Fig. S2a and b) can be attributed to 3d<sub>5/2</sub> and 3d<sub>3/2</sub> states of Sn(IV), respectively. The deoxidation degree of the graphitic layers before and after expansion can be estimated from C 1s spectra. As shown in Fig. 4c and d, the three deconvoluted peaks in the C1s spectra of SnO<sub>2</sub>/SIGO occur at 284.5, 286.2 and 288.1 eV. These peaks are usually assigned to the unoxidized graphite carbon skeleton (C-C, C=C and C vacancies), hydroxyl or epoxide group (C-OH or C-O-C), and carboxyl group (C=O), respectively.<sup>24,39</sup> The carbon to oxygen atomic ration R<sub>C/O</sub> in the graphitic sheets of SnO<sub>2</sub>/SIGO was calculated to be about 2.73:1, which increased to about

10.92:1 in GCSnO<sub>2</sub>, indicating a comparable reduction degree to the thermally treated GO (R<sub>C/O</sub>=9.7) under conditions of high temperature (~1050 °C) and rapid heating (~2000 °C/min).<sup>41,42</sup>

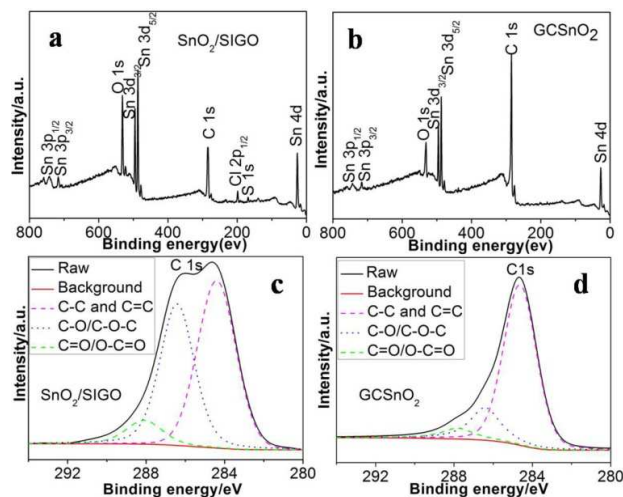


Fig. 4 Wide XPS spectra of the SnO<sub>2</sub>/SIGO (a) and GCSnO<sub>2</sub> (b); high-resolution XPS C1s spectra of SnO<sub>2</sub>/SIGO (c) and GCSnO<sub>2</sub> (d).

The morphology of the SnO<sub>2</sub>/SIGO and GCSnO<sub>2</sub> samples was observed by SEM and TEM. Fig.5a indicates that the SnO<sub>2</sub>/SIGO is very dense, which is in agreement with the BET analysis. The GCSnO<sub>2</sub> (Fig. 5b) displays a porous structure and wrinkled nature of thin graphene sheets. It is believed that most of the nano-SnO<sub>2</sub> particles are imbedded among the graphene sheets since few nanocrystals can be found on the outer surface of the GCSnO<sub>2</sub>.<sup>17,18</sup> Fig. 5c shows typical TEM image of GCSnO<sub>2</sub>, revealing that uniform nanocrystals of SnO<sub>2</sub> are distributed homogeneously. The inserted ring-like pattern of the selected-area electron diffraction (SAED) further confirms the presence of polycrystalline SnO<sub>2</sub>. The high magnification TEM image (Fig. 5d) indicates that the SnO<sub>2</sub> particles in GCSnO<sub>2</sub> are 5~10 nm in size; this is in agreement with the value calculated from XRD.

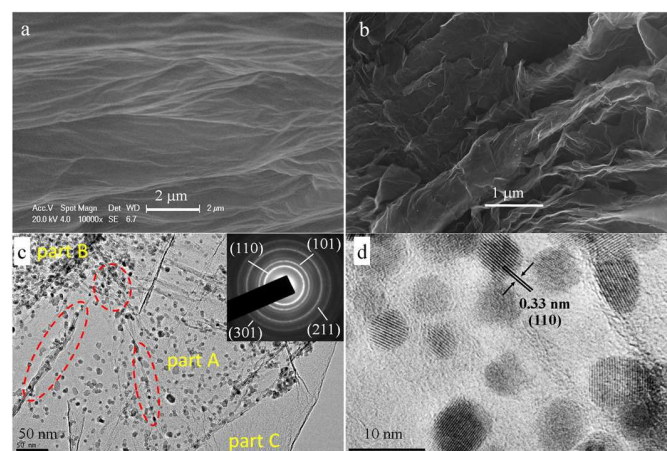


Fig. 5. a and b are SEM images of SnO<sub>2</sub>/SIGO and GCSnO<sub>2</sub>, respectively; (c, d) TEM images of the GCSnO<sub>2</sub> (inset of c is the corresponding SAED pattern of c).

As shown in Fig. 1, the SnO<sub>2</sub> nanoparticles coated on the surface of a multilayer SIGO particle, after expansion

exfoliation, the Nano-SnO<sub>2</sub> would mainly coat the outer layers of the graphene sheets. The high gas pressure driven recombination of these sheets from different SnO<sub>2</sub>/SIGO particles would result in the clamped structure. Fig. 5c and Fig. S3 both show three different morphologies marked as parts A, B, and C respectively. Part A is believed to be a single or few units of the GCSnO<sub>2</sub>. Some wrinkled regions as shown in the red cycles look like that the SnO<sub>2</sub> nanoparticles were trapped between two soft sheets. At the rim of part A (Fig. S3b), the curved layers of graphene around the SnO<sub>2</sub> particles also indicate a sandwiched structure.<sup>30</sup> This structure may prevent the SnO<sub>2</sub> nanoparticles from aggregating upon wringing and overlapping of the GCSnO<sub>2</sub> units as shown in part B. Part C displays a clean graphene sheet, which is expected to be reduced from an inner sheet of SIGO.

To further confirm the clamped nanostructure of the GCSnO<sub>2</sub>, etching experiments were carried out in 5 M HCl for 3 h under sonication. The ordinary graphene/nano-SnO<sub>2</sub> composite (O-G/SnO<sub>2</sub>), synthesized by the hydrolyzation of SnCl<sub>4</sub> in the presence of dispersed graphene, was also etched for comparison. The changes were analyzed by XRD (Fig. S4). The XRD peaks of SnO<sub>2</sub> in the O-G/SnO<sub>2</sub> decreased significantly, however, the XRD patterns of GCSnO<sub>2</sub> remained almost unchanged, indicating most of the SnO<sub>2</sub> nanoparticles were tightly coated by graphene.

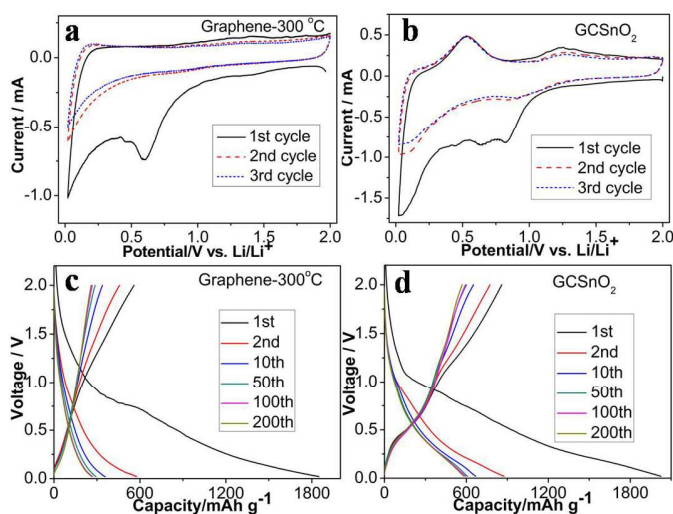


Fig. 6. a and b, CVs of the first three cycles of the graphene, GCSnO<sub>2</sub> and SnO<sub>2</sub> electrode in 1 mol/L LiPF<sub>6</sub>/EC+DMC+DEC at 0.1 mV/s. c and d are the voltage profiles of graphene, GCSnO<sub>2</sub> and pure SnO<sub>2</sub> electrode at 200 mA/g with the cycle number indicated.

Fig. 6a and b compare the CVs of graphene and GCSnO<sub>2</sub> (both prepared at 300 °C) in a electrolyte for lithium-ion batteries. There are several cathodic currents in the first cycle of graphene (Fig. 6a), which disappear in the subsequent cycles. This large irreversible capacity can be ascribed to several factors: the formation of the solid electrolyte interphase (SEI) layer, the reduction of residual surface-oxygenated groups on graphene sheets, and irreversible lithium insertion processes in graphene related carbonaceous materials.<sup>45-47</sup> For GCSnO<sub>2</sub> (Fig. 6b), the cathodic peak at potential of 0.80 V (vs. Li/Li<sup>+</sup>) was usually attributed to the reduction of the SnO<sub>2</sub> to Sn and Li<sub>2</sub>O (SnO<sub>2</sub> + 4Li<sup>+</sup> + 4e = 2Li<sub>2</sub>O + Sn), as well as the formation of SEI layer. These irreversible capacities might be compensated

by adding a small amount of lithium or lithium nitrides for the practical applications.<sup>48</sup>

Two corresponding anodic peaks are observed. One is at about 0.6 V, which can be attributed to de-alloying of Li<sub>x</sub>Sn. The other broad peak centered at about 1.24 V has been suggested to be the inverse reaction of SnO<sub>2</sub> reduction (2Li<sub>2</sub>O + Sn - 4e = SnO<sub>2</sub> + 4Li<sup>+</sup>), which is regarded as partially reversible.<sup>35</sup> From the second cycle, the highly reversible Li-alloying (cathodic peak at 0.1 V) and Li-dealloying (anodic peak at 0.6 V) become dominant for the capacitance contribution.

The galvanostatic discharge-charge tests of graphene (Fig. 6c) and GCSnO<sub>2</sub> (Fig. 6d) were carried out at a current density of 200 mA g<sup>-1</sup>. In line with the CV study, the potential platform above 0.8 V (vs. Li/Li<sup>+</sup>) in the first cathodic process of GCSnO<sub>2</sub> corresponds to the irreversible reduction of tin dioxide to metallic Sn and Li<sub>2</sub>O, together with the formation of SEI membranes.<sup>35</sup> From the second cycle, the cathodic branch of GCSnO<sub>2</sub> shows three main stages. The first stage, ending at about 1.0 V, may correspond to the reduction of residual SnO<sub>2</sub>. The second stage, centered at 0.5 V, is the Li-alloying reaction. The third stage, 0.15 V to 0.02 V, may be the contribution of Li-insertion reaction of graphene. The Li-alloying and dealloying reactions are very stable, indicating the highly dispersing of Sn nanoparticles in the composite. The first discharge and charge capacities of GCSnO<sub>2</sub> were 2054 and 858 mAh/g. In comparison, those of graphene are 1840 and 558 mAh/g. However, apart from the first discharge process, the reproducible shape of the charge and discharge curves illustrates the high reversibility of the electrode processes.

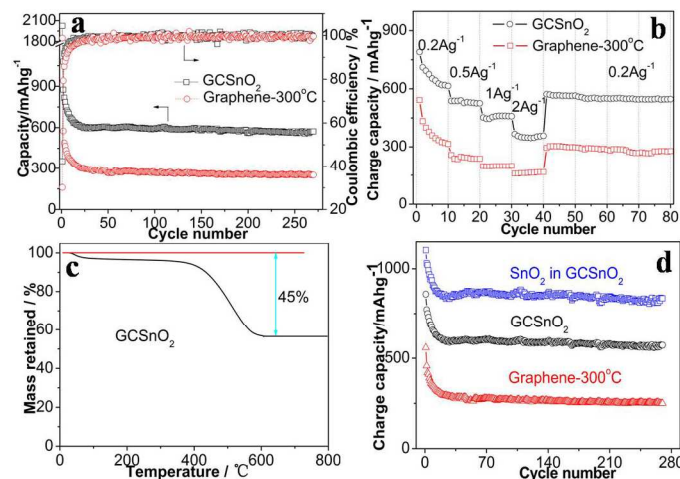


Fig. 7. a, Cycling performances and the corresponding coulombic efficiencies of the graphene and GCSnO<sub>2</sub> at a current density of 200 mA/g in the potential range of 0.02–2.00 V. b, Plots of charge capacity of graphene and GCSnO<sub>2</sub> cycled between 0.02 and 2.00 V (cell voltage) versus cycle number at different rates as indicated. c, TGA of GCSnO<sub>2</sub>. d, the capacity of SnO<sub>2</sub> in the GCSnO<sub>2</sub>.

Fig. 7a shows the cycling stability and coulombic efficiency of GCSnO<sub>2</sub> over 270 cycles at a current density of 200 mA/g in the potential range between 0.02 and 2.00 V. The charge capacity of GCSnO<sub>2</sub> decreases from 858 to 572 mAh/g at the 270th cycle, indicating less than 0.11% capacity loss per cycle. However, most of the capacity decay occurs in the first 10 cycles. As shown in Fig. 7a, the charge capacity of GCSnO<sub>2</sub> in

the 10<sup>th</sup> cycle is about 600 mAh/g and remains almost unchanged in the following 260 cycles. This cycling capacity and the retention rate are comparable to the best performances reported for SnO<sub>2</sub>/graphene (Table S1).<sup>23,24,32,49,50</sup> The coulombic efficiency of the GCSnO<sub>2</sub> increased from 42% to above 90% after the first cycle, and later increases to about 100% after 20 cycles. The graphene shows lower performances. Its charge capacity decays from 558 to 250 mAh/g during the 270 cycles, and its coulombic efficiency was also lower in the first 50 cycles.

To investigate the potential application of the GCSnO<sub>2</sub> for high power lithium-ion batteries, the rate performance was tested at current densities varying from 200 to 2000 mA/g (Fig. 7b). When the current was first increased from 200 to 500 mA/g, a stable capacity of around 520 mAh/g could be achieved. Afterwards, the rate was increased stepwise up to 2000 mA/g and the electrode could still deliver a stable capacity of about 360 mAh/g. When the current was set back to 200 mA/g, a capacity of 570 mAh/g could be restored and kept stable in the subsequent cycles. This demonstrates the good rate capability of GCSnO<sub>2</sub>. We postulate that the good conductivity of the graphene in the composite should be helpful to the rate performance.

Electrochemical impedance spectroscopy (EIS) measurements of the electrodes were carried out to understand the superior electrochemical performances of the GCSnO<sub>2</sub>. Fig. 8 compares the Nyquist plot of the electrode after 4 cycles at 200 mA/g to the plot after 80-cycle of rate testing as shown in Fig. 7b. Both plots are characteristic of one semicircle in the high frequency region and a straight sloping line in the low frequency region. They were almost the same, indicating that the as-formed SEI films in the initial cycles should be quite stable and remain unchanged during cycling at different rates.<sup>33</sup>

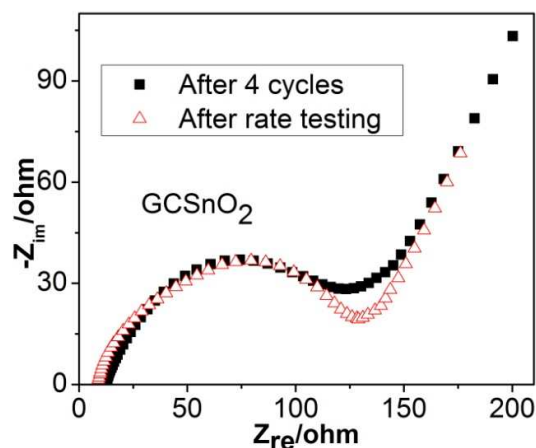


Fig. 8. Nyquist plots of GCSnO<sub>2</sub> electrode after 4 cycles at 200 mA/g (squares) and after 80 cycles of rate testing (triangles) as shown in Fig. 7b. Measured at the potential of 2.0 V.

Since both SnO<sub>2</sub> and graphene are electroactive, the electrochemical behavior of SnO<sub>2</sub> in the GCSnO<sub>2</sub> nanostructure was further investigated. The mass weight percentage of SnO<sub>2</sub> in the GCSnO<sub>2</sub> was about 55wt% as determined by thermogravimetric analysis (TGA, Fig. 7c), considering the final mass remaining after calcination in air should be pure SnO<sub>2</sub>. Assuming the total charge capacity is a sum of those from SnO<sub>2</sub>

and graphene, the contribution of SnO<sub>2</sub> in the composite can be estimated by the equation  $C_{\text{SnO}_2} = [C_{\text{GCSnO}_2} - 0.45C_{\text{graphene}}] / 0.55$ , where  $C_{\text{GCSnO}_2}$  and  $C_{\text{graphene}}$  are the specific discharge capacities of GCSnO<sub>2</sub> and graphene as shown in Fig. 7a. The calculated  $C_{\text{SnO}_2}$  together with  $C_{\text{GCSnO}_2}$  and  $C_{\text{graphene}}$  against cycling number were plotted in Fig. 7d. The first charge capacity of the SnO<sub>2</sub> in GCSnO<sub>2</sub> is about 1103 mAh/g; significantly larger than the theoretical reversible capacity of SnO<sub>2</sub> (782 mAh/g) when taking only the Li-alloying of Sn into account. This suggests that the oxidation of Sn to SnO<sub>2</sub> has partially occurred. Since the transforming reaction between SnO<sub>2</sub> and Sn is likely irreversible, this might have caused the capacity decay in the first 10 cycles. Over the following 260 cycles, the charge capacity of the SnO<sub>2</sub> kept about 800mAh/g, corresponding to a full and stable utilization of the theoretical reversible capacity of SnO<sub>2</sub>.

The excellent cyclic ability should be attributed to the special nanostructure of the GCSnO<sub>2</sub>. The graphene layers should work as a good barrier to prevent the Sn nanoparticles from aggregation. Fig. 9 shows typical TEM images of the GCSnO<sub>2</sub> electrode after 270 charge-discharge cycles at 200 mA/g. The images show that the nanoparticles remained highly dispersive in the graphene matrix. The SAED pattern suggests the nanoparticles are Sn in an amorphous structure (Fig. 9a). The sizes of Sn particles are around 10nm (Fig. 9b), which is very close to that of the initial particle size of SnO<sub>2</sub>, indicating no obvious aggregation occurred after the 270 cycles.

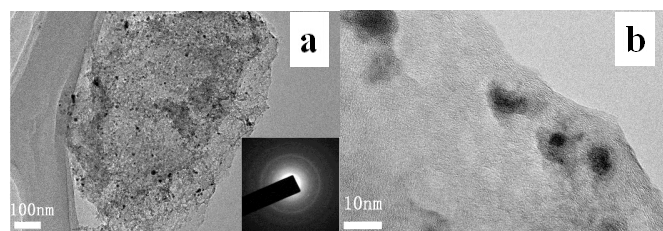


Fig. 9. a and b are the TEM images of the GCSnO<sub>2</sub> after 270 cycles (inset of image in Fig. 8a is its corresponding SAED pattern).

For comparison, pure Nano-SnO<sub>2</sub> (~10 nm in sizes) prepared through hydrolyzation of SnCl<sub>4</sub> was tested under similar conditions. The X-ray diffraction (XRD) patterns of pure nano-SnO<sub>2</sub> are shown in Fig. S5. The Nano-SnO<sub>2</sub> displayed an aggregation morphology under SEM and TEM observations (Fig. S6a and b).<sup>30</sup> Although it delivered an initial charge capacity of 953 mAh/g at 200 mA/g, the capacity declined quickly to about 150 mAh/g at the 50th cycle (Fig. S7). The O-G/SnO<sub>2</sub>, with the SnO<sub>2</sub> content (62 wt. %, Fig. S8a) comparable to that of GCSnO<sub>2</sub>, is basically uniform according to the SEM image (Fig. S8b). Some particles in the O-G/SnO<sub>2</sub> sample (presumably of SnO<sub>2</sub>) had not been sandwiched between the graphene sheets and can be seen on the surface of the graphene layers. This traditional process does not have a productive mechanism for the formation of graphen/SnO<sub>2</sub>/graphene sandwich structure. As a result, the O-G/SnO<sub>2</sub> performed better than the nano-SnO<sub>2</sub>, but exhibited much lower performance than GCSnO<sub>2</sub>. The charge capacity of O-G/SnO<sub>2</sub> faded to about 400 mAh/g after the 50th cycle (Fig. S7).

## Conclusions



A facile SIGO process was demonstrated for the synthesis of affordable graphene clamped SnO<sub>2</sub> nanostructured materials for lithium-ion batteries. The SIGO process proceeds in air and has several advantages. No reductant is used in the process. Operation is simple and requires only small amounts of energy. It is also environmentally friendly, and it can be readily adapted by industry. The initial reversible capacity of the resultant GCSnO<sub>2</sub> at a current density of 200 mAh/g was 858 mAh/g. After 270 discharge-charge cycles, it still had a capacity of 572 mAh/g. This corresponded to a capacity attenuation rate of only 0.11% per cycle. During cycling, all the theoretical capacity of SnO<sub>2</sub> relating to the Li-alloying and de-alloying of Sn can be fully and stably utilized. Furthermore, the GCSnO<sub>2</sub> show a good rate performance with a reversible capacity of 360 mAh/g at 2 A/g during the forty cycles studied. These findings suggest that both the SIGO process and the resultant GCNSnO<sub>2</sub> are promising for practical applications. The excellent electrochemical performances of GCSnO<sub>2</sub> composite can be attributed to the special nanostructure of the GCSnO<sub>2</sub>, in which the nanoparticles are strongly trapped between graphene sheets, hence almost no aggregation of nano-Sn was found after the 270 cycles.

### Acknowledgements

This work is supported by NSFCs (21173161, 20973130), the 863 project (2009AA03Z503), the MOE Program (NCET-11-0397), the Fundamental Research Funds for the Central Universities of Wuhan University.

### Notes and referents

<sup>1</sup> College of Chemistry and Molecular Sciences, Hubei Key Laboratory of Electrochemical Power Sources, Wuhan University, Wuhan, 430072, P.R. China. <sup>2</sup> Oak Ridge National Laboratory, Oak Ridge, TN 37831, USA

\* To whom correspondence should be addressed.

E-mail: [whu\\_wangzy@sina.com](mailto:whu_wangzy@sina.com) (ZYW) and [xbjin@whu.edu.cn](mailto:xbjin@whu.edu.cn) (XBJ)

A/Professor Xianbo Jin, Associate Professor Zhiyong Wang

- R. K. Selvan, I. Perelshtein, N. Perkas and A. Gedanken, *J. Phys. Chem. C* 2008, **112**, 1825.
- H. Liu and Q. Wan, *Nanoscale* 2012, **4**, 4481.
- X. S. Fang, J. Yan, L. F. Hu, H. Liu and P. S. Lee, *Adv. Func. Mater.* 2012, **22**, 1613.
- H. Liu, J. X. Wan, Q. Y. Fu, M. Li, W. Luo, Z. P. Zheng, H. F. Cao, Y. X. Hu and D. X. Zhou, *Sens. Actuators, B* 2013, **177**, 460.
- M. Armand and J. M. Tarascon, *Nature* 2008, **451**, 652.
- M. H. Liang and L. J. Zhi, *J. Mater. Chem.* 2009, **19**, 5871.
- Y. Idota, T. Kubota, A. Matsufuji, Y. Maekawa and T. Miyasaka, *Science*, 1997, **276**, 1395.
- X. W. Lou, D. Deng, J. Y. Lee and L. A. Archer, *Chem. Mater.*, 2008, **20**, 6562.
- P. Meduri, C. Pendyala, V. Kumar, G. U. Sumanasekera and M. K. Sunkara, *Nano Lett.* 2009, **9**, 612.
- J. S. Chen and X. W. Lou, *Small*, 2013, **9**, 1877.
- Z. P. Guo, G. D. Du, Y. Nuli, M. F. Hassan and H. K. Liu, *J. Mater. Chem.* 2009, **19**, 3253.
- J. Y. Zhang, Z. Y. Wang, Y. Z. Hong, S. X. Li, X. B. Jin and Z. C. George, *Electrochem. Commun.* 2014, **38**, 36.
- J. Liu, W. Li, A. Manthiram, *Chem. Commun.* 2010, **46**, 1437.
- C. C. Chang, Y. C. Chen, C. W. Huang, Y. H. Su and C. C. Hu, *Electrochim. Acta* 2013, **99**, 69.
- K. S. Novoselov, A. K. Geim, S. V. Morozov, D. Jiang, Y. Zhang, S. V. Dubonos, I. V. Grigorieva and A. A. Firsov, *Science* 2004, **306**, 666.
- Z. S. Wu, W. Ren, L. Wen, L. Gao, J. Zhao, Z. Chen, G. Zhou, L. Feng and H. M. Cheng, *ACS nano* 2010, **4**, 3187.
- X. S. Zhou, L. J. Wan and Y. G. Guo, *Adv. Mater.* 2013, **25**, 2152.
- J. Yao, X. P. Shen, B. Wang, H. K. Liu and G. X. Wang, *Electrochem. Commun.* 2009, **11**, 1849.
- D. Wang, R. Kou, D. Choi, Z. Yang, Z. Nie, J. Li, L. V. Saraf, D. Hu, J. Zhang, G. L. Graff, J. Liu, M. A. Pope and I. A. Aksay, *ACS nano* 2010, **4**, 1587.
- J. S. Zhu, D. L. Wan, L. Wang, X. S. Liang and W. L. You, *Electrochim. Acta* 2013, **91**, 323.
- P. C. Lian, J. Y. Wang, D. D. Cai, L. X. Ding, Q. M. Jia and H. H. Wang, *Electrochim. Acta* 2014, **116**, 103.
- S. J. Prabakar, Y. H. Hwang, E. G. Bae, S. Shim, D. Kim, M. S. Lah, K. S. Sohn and M. Pyo, *Adv. Mater.* 2013, **25**, 3307.
- X. Zhu, Y. Zhu, S. Murali, M. D. Stoller and R. S. Ruoff, *J. Power Sources* 2011, **196**, 6473.
- S. K. Park, S. H. Yu, N. Pinna, S. Woo, B. Jang, Y. H. Chung, Y. H. Cho, Y. E. Sung and Y. Z. Piao, *J. Mater. Chem.* 2012, **22**, 2520.
- L. Wang, D. Wang, Z. H. Dong, F. X. Zhang and J. Jin, *Nano Lett.* 2013, **13**, 1711.
- J. L. Cheng, H. L. Xin, H. M. Zheng and B. Wang, *J. Power Sources* 2013, **232**, 152.
- N. I. Kovtyukhova, P. J. Ollivier, B. R. Martin, T. E. Mallouk, S. A. Chizhik, E. V. Buzaneva and A. D. Gorchinskiy, *Chem. Mater.* 1999, **11**, 771.
- J. P. Rourke, P. A. Pandey, J. J. Moore, M. Bates, I. A. Kinloch, R. J. Young and N. R. Wilson, *Angew. Chem. Int. Ed.* 2011, **123**, 3231.
- J. F. Liang, Y. Zhao, L. Guo and L. D. Li, *ACS appl. Mater. interfaces* 2012, **4**, 5742.
- X. Wang, X. Cao, L. Bourgeois, H. Guan, S. Chen, Y. Zhong, D. Tang, H. Li, T. Zhai, L. Li, Y. Bando and D. Golberg, *Adv. Funct. Mater.* 2012, **22**, 2682.
- W. B. Yue, S. Yang, Y. Ren and X. J. Yang, *Electrochim. Acta* 2013, **92**, 412.
- S. M. Paek, E. Yoo and I. Honma, *Nano Lett.* 2008, **9**, 72.
- X. Zhou, Y. X. Yin, L. J. Wan and Y. G. Guo, *J. Mater. Chem.* 2012, **22**, 17456.
- P. Lian, X. Zhu, S. Liang, Z. Li, W. Yang and H. Wang, *Electrochim. Acta* 2011, **56**, 4532.
- Y. Zhu, C. Li and C. Cao, *RSC Adv.* 2013, **3**, 11860.
- B. P. Vinayan and S. Ramaprabhu, *J. Mater. Chem. A* 2013, **1**, 3865.
- C. Xu, J. Sun and L. Gao, *J. Mater. Chem.* 2012, **22**, 975.
- Y. Su, S. Li, D. Wu, F. Zhang, H. Liang, P. Gao, C. Cheng and X. Feng, *ACS nano* 2012, **6**, 8349.
- Y. Z. Hong, Z. Y. Wang and X. B. Jin, *Sci. Rep.* 2013, **3**, 3439.
- W. S. Hummers and R. E. Offeman, *J. Am. Chem. Soc.* 1958, **80**, 1339.
- H. C. Schniepp, J. L. Li, M. J. McAllister, H. Sai, M. Herrera-Alonso, D. H. Adamson, R. K. Prud'homme, R. Car, D. A. Saville and I. A. Aksay, *J. Phys. Chem. B* 2006, **110**, 8535.

- 42 M. J. McAllister, J. L. Li, D. H. Adamson, H. C. Schniepp, A. A. Abdala, J. Liu, M. Herrera-Alonso, D. L. Milius, R. Car, R. K. Prud'homme and I. A. Aksay, *Chem. Mater.* 2007, **19**, 4396.
- 43 A. B. Bourlinos, D. Gournis, D. Petridis, T. Szabó, A. Szeri and I. Dékány, *Langmuir* 2003, **19**, 6050.
- 44 H. L. Wang, J. T. Robinson, X. L. Li and H. J. Dai, *J. Am. Chem. Soc.* 2009, **131**, 9910
- 45 C. T. Hsieh, C. Y. Lin, Y. F. Chen, J. S. Lin and H. Teng, *Carbon* 2013, **62**, 109.
- 46 H. Liu, J. Huang, X. Li, J. Liu, Y. Zhang and K. Du, *Appl. Surf. Sci.* 2012, **258**, 4917.
- 47 H. K. Zhang, H. H. Song, X. H. Chen, J. S. Zhou and H. J. Zhang, *Electrochim. Acta* 2012, **59**, 160.
- 48 J. Yang, Y. Takeda, N. Imanishi, T. Ichikawa, O. Yamamoto, *Solid State Ionics* 2000, 135, 175–180.
- 49 X. Wang, X. Zhou, K. Yao, J. Zhang and Z. Liu, *Carbon* 2011, **49**, 133.
- 50 M. Zhang, D. Lei, Z. Du, X. Yin, L. Chen, Q. Li, Y. Wang and T. Wang, *J. Mater. Chem.* 2011, **21**, 1673.